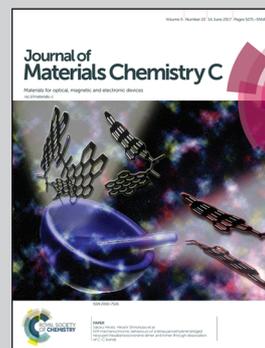


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On the chemically-assisted excitonic enhancement in environmentally-friendly solution dispersions of two-dimensional MoS_2 and WS_2

From ultraviolet to the near infrared, ideal solvent chemistries enhance excitonic effects in solution dispersions of two-dimensional layered refractory sulfides, which yield high-performance p-n junctions. These dispersions can pave the way for enabling other novel optoelectronic devices from such nanoscale materials, albeit in a low-cost, scalable manufacturing platform.

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On the chemically-assisted excitonic enhancement in environmentally-friendly solution dispersions of two-dimensional MoS₂ and WS₂

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Current rectifying p–n junction devices are demonstrated from solution exfoliated two-dimensional (2D) molybdenum disulfide (MoS₂), and excitonic effects are elucidated for solution dispersions of not only MoS₂, but also another refractory 2D sulfide, tungsten disulfide (WS₂). The excitonic enhancement effects are correlated to new solution chemistries using environmentally friendly terpeneol. The role of sonication time and centrifugation are analyzed in the presence of terpeneol with isopropyl alcohol and surfactant ethyl cellulose, where the red-shift in the excitonic peaks is correlated to the size distribution of the nanoparticles using optical interferometry. This was correlated to the data obtained using photoluminescence, Raman spectroscopy, scanning electron microscopy and particle size analysis which also yielded results that were consistent with this finding. The terpeneol dispersion exhibits the least red-shift of 5 meV from the top to the bottom of the vial, in contrast to non-terpeneol dispersions where the red-shift is calculated to be as high as 90 meV, indicating terpeneol's effectiveness in exfoliating a larger population of mono- to few-layer nanomembranes. Analysis of the optical absorption spectra allows for the extraction of the energy band gap for MoS₂ and WS₂. These results clearly show evidence of quantum confinement effects in solution dispersions of chemically exfoliated 2D MoS₂ and WS₂ which can be harnessed for a wide variety of optoelectronic devices that are amenable to scalable and high-throughput synthesis routes, using environmentally friendly solution chemistries.

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1. Introduction

Two-dimensional (2D) layered materials (LMs) such as graphene and transition metal dichalcogenides (TMDCs) have been the focus of intense research recently due to their interesting optical, electronic, thermal and mechanical properties that are paving the way for new device platforms.^{1–3} For example, thin film transistors,⁴ supercapacitors,⁵ biosensors,⁶ and a wide variety of other electronic, optoelectronic and sensing modalities have been enabled by 2DLMs.^{7–9} The d-orbital conductivity of the transition metal M in the formation of the TMDC with stoichiometry MX₂, where X is a group VI chalcogen atom (S, Se or Te), gives some TMDCs interesting optical properties. Non-conventional antimonene and arsenene 2D semiconductors with tunable band gap have also been predicted and explored for optoelectronic devices.^{10,11} In some 2DLMs, the band gap E_g typically increases with decreasing layer number, and a transition from indirect band gap to direct band gap is observed in the limit of monolayers. For example, TMDCs such as MoS₂ and WS₂ have E_g (indirect) \sim 1.2 eV and 1.4 eV in the bulk, respectively,

whereas E_g increases to 1.8–1.9 eV and 1.9–2.1 eV for monolayers, respectively, and is also a direct gap in this limit.^{12,13} Moreover, light emission measurements conducted on MoS₂ and WS₂ in the visible regime are suggestive of excitonic effects emergent in these materials.^{14,15} Such excitonic effects are presumed to arise when an electron (e) is promoted to the conduction band (CB), leaving a hole (h) in the valence band (VB) after the optical absorption of a photon with energy $E > E_g$. Given the strong attractive Coulombic interaction in the quantum confinement limit of 2D nanosheets, this e–h pair, or exciton, is bound together with relatively large binding energies at room temperature, and provides certain 2DLMs with unique optical and optoelectronic properties. While excitonic effects have been observed in mechanically exfoliated monolayers of 2D MoS₂,¹² as well as chemically dispersed solutions,^{16,17} here we provide an in-depth analysis of excitonic and hot luminescence effects that are observed in solution-dispersed, chemically exfoliated 2D MoS₂ and WS₂ from bulk crystals using environmentally friendly and biodegradable terpeneol (T). Terpeneol not only acts as a stabilizer but also seems to play a role in the effective exfoliation of the bulk crystallites. Such solution-based approaches provide advantages in terms of scalability and high throughput synthesis routes, and the use of environmentally-friendly,

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biodegradable materials makes such dispersions attractive for sustainability and additive manufacturing practices, for example with the use of ink jet printing, which results in little material waste. At the same time, these dispersions based on terpeneol provide an avenue to access the unique optical and opto-electronic properties emergent in the quantum regime, as exemplified by the excitonic effects observed here, for the realization of high-performance devices, compared to mechanical exfoliation that is clearly not amenable to scalability.

Just as the weak van der Waals interaction between the layers in 2DLMs allows these materials to be mechanically exfoliated into individual layers from the bulk crystal with ease,^{1,13,18} chemicals – in conjunction with mechanical agitation – can have a similar effect to shear the layers to yield nanosheets and even monolayers in solution.¹⁹ This approach is versatile, low-cost and can provide a sustainable route to the production of 2D nanosheets for device applications, including opening up prospects for the realization of functional structures on flexible, light-weight or transparent substrates. In order to disperse the 2DLMs in solution, ultrasonication is a commonly used approach to separate the bulk crystal into 2D nanosheets through high-energy jets that provide mechanical agitation, concurrent to the chemical action engendered by the dispersion solvent. Besides the ultrasonication conditions (power, time, frequency, *etc.*), the choice of solvent is also an important factor in determining the effectiveness of the dispersions, where some organic solvents have been shown to have cohesive energies close to the interlayer energies of 2DLMs.²⁰

In this work, we have provided an in-depth analysis of the excitonic effects emergent in 2D MoS₂, as well as the less studied WS₂ system for the first time, which is dispersed in isopropanol (IPA), and the role of ethyl cellulose (EC) as a surfactant, and terpeneol (T) is also explored. After sonication, the samples are centrifuged as noted in prior work to further mass-separate the dispersion,^{19,21–23} presumably leaving monolayers to

few layer nanosheets at the top of the vial, while the thicker or bulk flakes appear at the bottom. From the optical absorption spectra we not only characterize the location of the excitonic peaks that are a signature of hot-luminescence effects in MoS₂ and WS₂, but also compare the difference in E_g values obtained for nanosheets from the top to the bottom of the vial, for the first time. Structural characterization to infer the layer number and particle size was performed using photoluminescence (PL), Raman spectroscopy, scanning electron microscopy (SEM) and laser interferometry. The particle size analysis yielded a distribution of particle size for the two populations: samples taken from the top and bottom of the vial. The electronic transport in 2D MoS₂ dispersions is also analyzed and compared to that in mechanically exfoliated MoS₂, from which p–n junction behavior is noted for solution dispersed MoS₂ on p-type Si substrates. We believe that in the solution dispersions of MoS₂ where the excitonic peaks are amplified, such as in the terpeneol based samples, the ensuing electron transport measurements also reveal enhanced device figures of merit for p–n junction devices compared to dispersions without terpeneol. The comprehensive optical and electronic characterization of solution dispersed 2DLMs, particularly using the environmentally friendly solutions discussed in this work, should lay the foundation for the design of high-performance electronic and optoelectronic devices in the future.

2. Results and discussion

The MoS₂ and WS₂ bulk crystals were dispersed in vials at a concentration of 5 mg mL⁻¹, as shown in Fig. 1, using a combination of solvent IPA, surfactant EC, and stabilizer T. In prior work, both EC and T have been known to minimize nanomembrane re-aggregation.²⁴ The specific dispersion conditions for samples S1, S2, S3, S4, S5 and S6 are provided in Table 1 at two

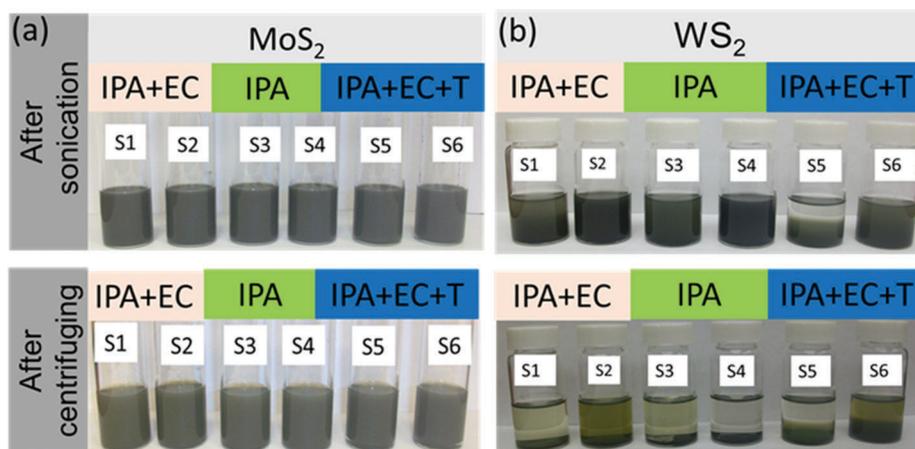


Fig. 1 Visual images of MoS₂ and WS₂ sample dispersions under the same conditions as noted for S1–S6. (a) MoS₂ after sonication in solvents (top) and after centrifugation in the same solvents at 2000 rpm (bottom). S1 and S2 correspond to dispersions prepared in IPA and EC at $t_{\text{sonic}} \sim 99$ min and 297 min, respectively. S3 and S4 correspond to dispersions prepared in IPA only at $t_{\text{sonic}} \sim 99$ min and 297 min, respectively. S5 and S6 correspond to dispersions prepared in IPA, EC and T at $t_{\text{sonic}} \sim 99$ min and 297 min, respectively (see Table 1). (b) WS₂ after sonication in solvents (top) and after centrifugation in the same solvents at 2000 rpm (bottom) under the same conditions as noted in (a) for MoS₂.

Table 1 Solution dispersions S1–S6 for MoS₂ and WS₂ at two sonication times (t_{sonic})

	Dispersion mixtures	t_{sonic} (min)
S1	2D material (50 mg) based on EC (5 mg) + IPA (10 mL)	99
S2	2D material (50 mg) based on EC (5 mg) + IPA (5 mL)	297
S3	2D material (50 mg) based on IPA (10 mL)	99
S4	2D material (50 mg) based on IPA (10 mL)	297
S5	2D material (50 mg) based on EC (5 mg) + IPA (5 mL) + T (5 mL)	99
S6	2D material (50 mg) based on EC (5 mg) + IPA (5 mL) + T (5 mL)	297

different sonication times t_{sonic} . Here, S1 and S2 represent dispersions formed using IPA and 3% EC surfactant at $t_{\text{sonic}} \sim 99$ min and 297 min, respectively; S3 and S4 are formed using IPA only at $t_{\text{sonic}} \sim 99$ min and 297 min, respectively; and S5 and S6 are formed using IPA, EC (3%) and T at a $t_{\text{sonic}} \sim 99$ min and 297 min, respectively. After sonication, the dispersions were centrifuged at 2000 rpm (805 rcf) for 30 min, and distinct differences could be seen in the MoS₂ and WS₂ solutions (Fig. 1). The WS₂ dispersions have a discernable color difference after centrifugation (Fig. 1b-bottom), which is likely related to the high degree of exfoliation and small lateral sizes of the nanosheets.^{16,17} Interestingly, unlike the WS₂ dispersions, the separation and the change in color contrast in the MoS₂ samples (Fig. 1a-bottom) is less pronounced after centrifugation under the same dispersion conditions, which is likely to do with

the higher mass of WS₂, increasing the likelihood of the WS₂ flakes settling at the bottom of the vial, unlike the lighter MoS₂ flakes which are likely to be more homogeneously dispersed.

In order to investigate the optical properties of the 2D exfoliated solution dispersions, optical absorption spectra were obtained using a CARY UV-vis-NIR spectrophotometer. Given that there is a density band sedimentation gradient from top to bottom, we have analyzed the optical absorption characteristics of the dispersions taken from the two locations, *i.e.* the top and bottom of the vial, as shown in Fig. 2a and (b) for MoS₂ and WS₂, respectively. In the MoS₂ dispersions (Fig. 2a(i)–(iii)), at a fixed sonication time of 297 min (*i.e.* S2, S4 and S6), two distinct absorption peaks appear at energies $E_A \sim 1.83$ eV and $E_B \sim 2$ eV. As has been noted in prior work,^{12,19,25} these peaks are the excitonic A and B peaks that occur at energies E_A and E_B , respectively, and are

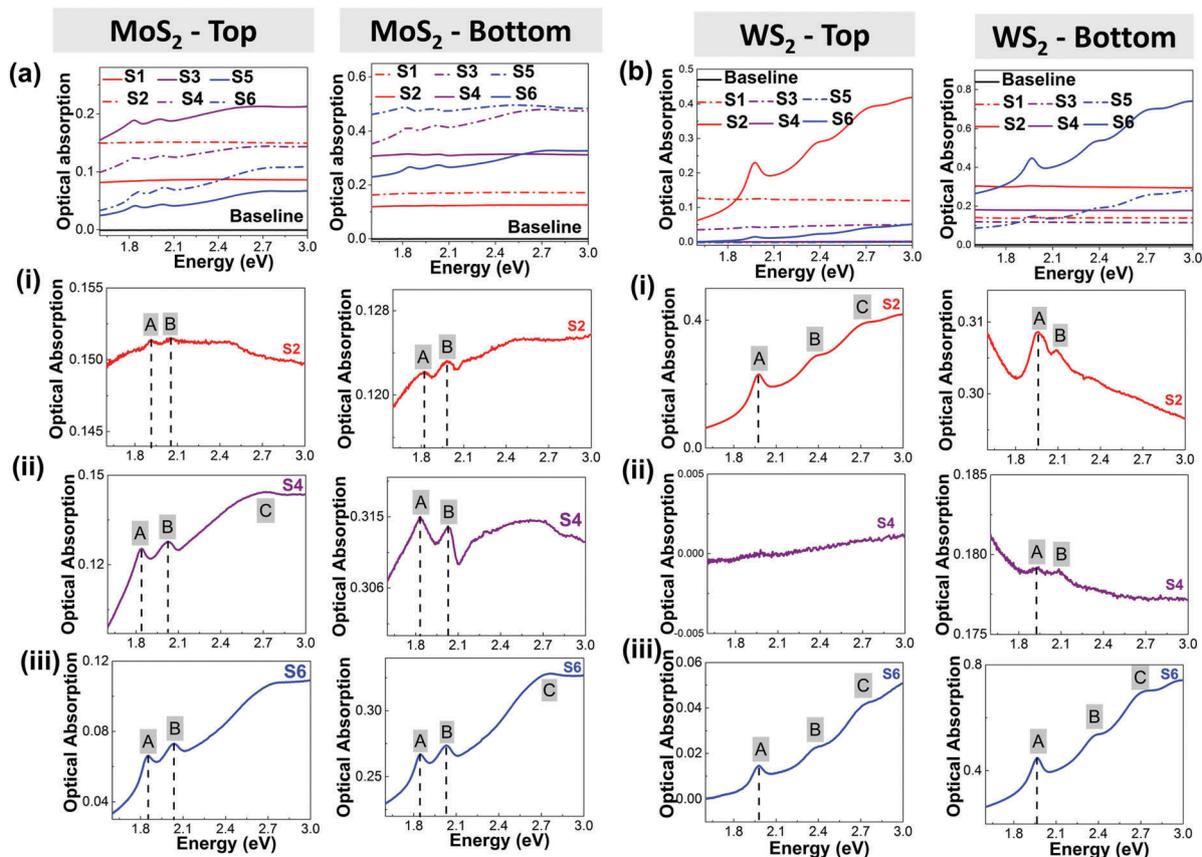


Fig. 2 Optical absorption spectra taken from the top and bottom of the vial for (a) MoS₂ and (b) WS₂. (a) (left) Samples taken from the top of the vial, and (right) bottom of the vial for MoS₂. (b) (left) Samples taken from the top of the vial, and (right) bottom of the vial for WS₂. The dashed line corresponds to a 99 min period of sonication and the continuous line corresponds to 297 min of sonication. (i–iii) represent more details of the absorption in the S2, S4, and S6 solutions.

an outcome of direct hot luminescence effects for our solution dispersed MoS₂. Here, direct gap transitions occur at the *K*-point of the Brillouin zone between the VB maxima and the CB minima. From the analysis of the data in Fig. 2a(i)–(iii), the value of the excitonic *A* peak measured for the solution at the top $E_A(\text{top})$ is greater than the excitonic *A* peak measured for the solution at the bottom $E_A(\text{bottom})$. Our analysis reveals that there is a red-shift in the excitonic peak location, as we go from top to bottom, *i.e.* $E_A(\text{top}) > E_A(\text{bottom})$ in most of the solution dispersions we have explored. For example, through our measurements $\Delta E_A = E_A(\text{top}) - E_A(\text{bottom})$ was calculated to be 90 meV, 11 meV and 5 meV for samples in the S2, S4 and S6 dispersions, respectively. The terpeneol-based dispersion, S6, exhibited the least red-shift of 5 meV from the top to the bottom of the vial, in contrast to the non-terpeneol dispersions, S2 and S4, where the red-shift is as high as 90 meV, indicating terpeneol's effectiveness in exfoliating a larger population of mono- to few-layer nanomembranes. Moreover, Shi *et al.*¹⁸ also observed a red-shift in E_A in bulk MoS₂ in comparison to mechanically exfoliated monolayer MoS₂. Our optical absorption spectra corroborate the quantum confinement induced effects that we have observed while noting the shift in the excitonic peak location that arises after centrifugation where the smaller and thinner flakes are at the top of the vial and the larger flakes are at the bottom.

Similarly, the WS₂ dispersions (Fig. 2b(i)–(iii)) show the excitonic *A* peak at $E_A \sim 1.97$ eV; interestingly no excitonic peaks are observed in the S4 dispersion at the top, and at the same time, very weak excitonic *A* and *B* peaks are seen at the bottom in this case. Additionally, the excitonic *B* peak in WS₂ appears at $E_B \sim 2.34$ eV which is weaker in amplitude when compared to the excitonic *B* peak in MoS₂ in samples S2, S4 and S6 for both the top and bottom cases (Fig. 2b(i)–(iii)). The locations of the E_A and E_B excitons from the literature are found to be 2.0 eV and 2.4 eV, respectively, for monolayers of mechanically exfoliated WS₂ which are comparable to the values we have obtained here in our solution dispersions of WS₂.²⁶ Under certain conditions, the excitonic *C* peak is also seen in WS₂ that has been attributed to Van Hove singularities which occur at critical points in the density of states, and can lead to strong optical absorption effects.²⁷ Here, we do indeed observe the excitonic *C* peak at $E_C \sim 2.72$ eV, which is only evident in the S2 (top) and S6 solution dispersions (top and bottom), corroborating the effective role of the EC + T in exfoliating and dispersing the 2DLMs. Interestingly, the optical images of the vials in Fig. 1b for WS₂ reveal that S2 and S6 samples are darker in color compared to the other dispersions (S1, S3, S4 and S5) after centrifugation, which may be an artifact of the strong optical absorption effects arising from the Van Hove singularities characteristic of the excitonic *C* peak in these specific dispersions. Moreover, $E_A(\text{top}) > E_A(\text{bottom})$ for the excitonic *A* peak of WS₂, where $\Delta E_A = E_A(\text{top}) - E_A(\text{bottom})$ was computed to be 12 meV for solution dispersions S2 and S6.

In general, from our analysis, it appears that the solution dispersions S5 and S6 formed using T appear to amplify the excitonic behavior of MoS₂, while similar effects are certainly

noted for WS₂ in S6. The role of EC and T also seems to be important in enhancing the dispersibility of MoS₂ and WS₂, while at the same time minimizing re-agglomeration of the 2D nanoflakes.¹⁵ In certain mixtures, *e.g.* S2 and S4 for WS₂ (*i.e.* Fig. 2b(i) and (ii) (right)), the absorbance of the bottom sample shows a reverse trend, in that the absorbance increases into the IR regime (lower energies) which may be due to defect states that arise in the mid-gap regime under these conditions. Another possibility is related to the poor exfoliation of the flakes which settle at the bottom.¹⁶ A more detailed analysis is necessary to corroborate this however.

We have estimated the E_g of solution-dispersed MoS₂ and WS₂ by using the optical absorption spectra and fitting these spectra to the Tauc model.²⁸ This technique has been valuable in estimating the optical properties of other nanostructured materials, such as TiO₂ nanoparticles, ZnS quantum dots, and CdSe films.^{29,30} In our implementation of this model to the solution dispersed MoS₂ and WS₂, the absorbance *A* from the optical spectra shown in Fig. 2 is used to plot $(\alpha h\nu)^2$ as a function of *E*, where $\alpha = 2.303 \times A/d$ from the Lambert-Beer-Lambert law; here *d* = 1 mm is the path length of the glass slide, *h* is Planck's constant, and ν is the incoming photon frequency in our spectrophotometer. As shown in Fig. 3a and b, E_g is then extracted from the *x*-intercept of the $(\alpha h\nu)^2$ versus *E* plot. Using this model, we have also considered the scenario assuming an indirect band gap of our 2DLM dispersion, where the exponent *n* in $(\alpha h\nu)^n$ is taken to be $\frac{1}{2}$.³¹ However, this yielded a poor fit and the linear extrapolation did not intersect with the *E*-axis, lending support to the fact that our 2D MoS₂ and WS₂ dispersions indeed yield direct band gap optical absorption characteristics that are induced by quantum confinement effects.

Although Woomey *et al.* have shown a limitation of the Tauc model for the determination of E_g in 2D-black phosphorus,³² in our fitting analysis we have conducted the fit outside of the regions in the *E*-axis where the *A* and *B* excitonic peaks emerge, and before the area where the *C* peak is presumed to arise, as shown in Fig. 3a and b. These data also indicate the reproducibility of the E_g calculation from the error bars calculated from the standard deviation of each mean gap energy value. This illustrates that the $E_g(\text{top})$ in general appears to be higher for the solution taken from the top of the vial for both MoS₂ and WS₂, compared to the $E_g(\text{bottom})$ calculation. This is in agreement with the notion that the nanosheets at the top will tend to be thinner after centrifugation, and hence $E_g(\text{top}) > E_g(\text{bottom})$ due to quantum confinement effects. Moreover, the magnitude of the mean variation $\Delta E_g = E_g(\text{top}) - E_g(\text{bottom})$ appears to be larger in WS₂ compared to MoS₂, as shown in Fig. 3c and d, which may be visualized by the distinct color difference of the vials after centrifugation for WS₂ in contrast to MoS₂, for which the color did not change to a large extent after centrifugation (Fig. 1).

The excitonic peak locations shown in Fig. 2 and E_g calculations in Fig. 3 were based on optical absorption spectroscopy measurements. Optical absorption spectroscopy in the UV-visible-NIR regime is a powerful technique and is commonly used to measure the absorption properties of 2D materials to highlight

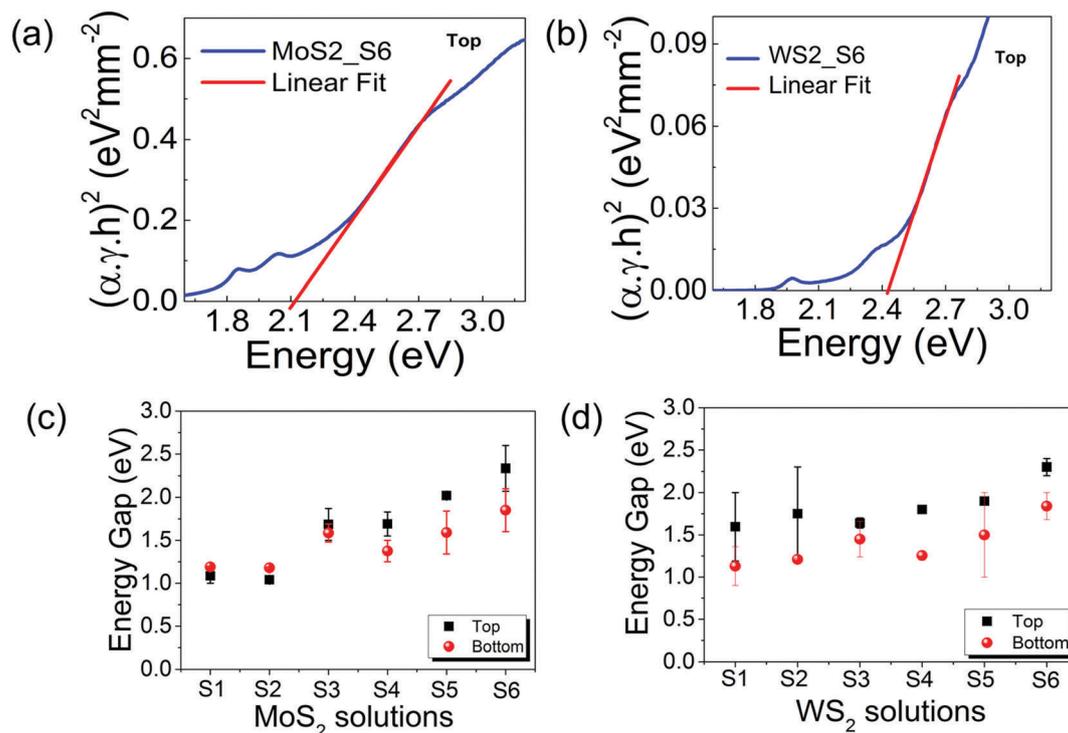


Fig. 3 Band gap E_g extraction from fitting to the Tauc model in the presence of excitonic peaks in solution S6 for (a) MoS₂ and (b) WS₂ dispersions. Tabulation of E_g obtained from the top and bottom of the solution dispersions for (c) MoS₂ and (d) WS₂ showing that E_g (top) generally tends to be larger than E_g (bottom) for most of the dispersions. Error bars represent the standard deviation of the mean value of the energy gap.

the existence of excitonic effects. For example, in early reports by Mak *et al.*,¹² optical absorption spectroscopy was used to study excitonic effects in mechanically exfoliated MoS₂, and follow-on work by Shi *et al.* in 2013¹⁸ revealed the existence of excitons in suspended mono- and multilayer 2D materials using optical absorption spectroscopy, where red shift effects were also noted. We have also conducted photoluminescence (PL) measurements on our dispersions to support the findings obtained using optical absorption spectroscopy, as noted by the data in Fig. 2 and 3 for both MoS₂ and WS₂. We have conducted this PL analysis as a function of solvent chemistries S1 (without terpineol) and S6 (with terpineol) to examine excitonic effects in semiconducting MoS₂ and WS₂ using PL, where samples of the dispersions were taken from the top of the vial and compared to those obtained from the bottom of the vial.

Fig. 4(a)–(g) shows the PL, Raman spectroscopy, high resolution SEM and particle size data for MoS₂ and WS₂. In particular, in Fig. 4a and b, we provide the PL data corresponding to solution chemistry S1 (without Terpineol) and S6 (with terpineol) for MoS₂, respectively, where the black spectra represent data gathered for MoS₂ nanomembranes taken from the top of the vial, and the red spectra correspond to those taken from the bottom of the vial. These peaks are labelled as indirect I peaks for the bottom samples I_b , and the samples from the top I_t , while the A and B excitonic peaks, which represent direct band gap optical transitions, are labelled as A_T and A_B for A -excitonic peaks for the top and bottom, respectively, while B_T and B_B correspond to the B -excitonic peaks for top

and bottom, respectively. As is apparent from Fig. 4a, the peak coinciding with that of the monolayer emission A -peak,³³ we see a significant red shift from $A_T \sim 1.86$ eV and $A_B \sim 1.80$ eV, where broadening effects are also apparent for the A_B peak. This suggests that the dispersion chemistry S1 is not effective in exfoliating the material given the significant red-shift of ~ 60 meV between the top and bottom ($1.86 - 1.80$ eV = 60 meV) which is consistent with the thicker material at the bottom approaching the bulk. Incidentally, the red-shift computed for non-terpineol based dispersions using optical absorption spectroscopy was computed to be 100 meV, in close agreement with the PL data. The indirect-gap PL peak at $I_B \sim I_T = 1.28$ eV becomes more pronounced as the thickness increases which is once again an indication that the material taken from the bottom is composed of thicker layers than the material taken from the top. In contrast, in Fig. 4b, which represents PL data obtained for solution chemistry S6 for MoS₂, terpineol appears to be effective in yielding a fewer layered material, even for samples taken from the bottom of the vial, where the red-shift effects are minimal since the locations of A_T and A_B occur at 1.87 eV. Moreover, there is also minimal broadening in the A_B peak in Fig. 4b, representing the monolayer emission peak.

Similarly for WS₂ where data are shown in Fig. 4c–d, the S1 sample in Fig. 4c indicates a large indirect I_b peak at 1.44 eV for the material taken from the bottom, characteristic of a thicker material. The A -excitonic peaks at the top and bottom occur at $A_T = 1.85$ eV and $A_B = 1.84$ eV, respectively, suggestive of a very small red-shift of 10 meV between the top and bottom.

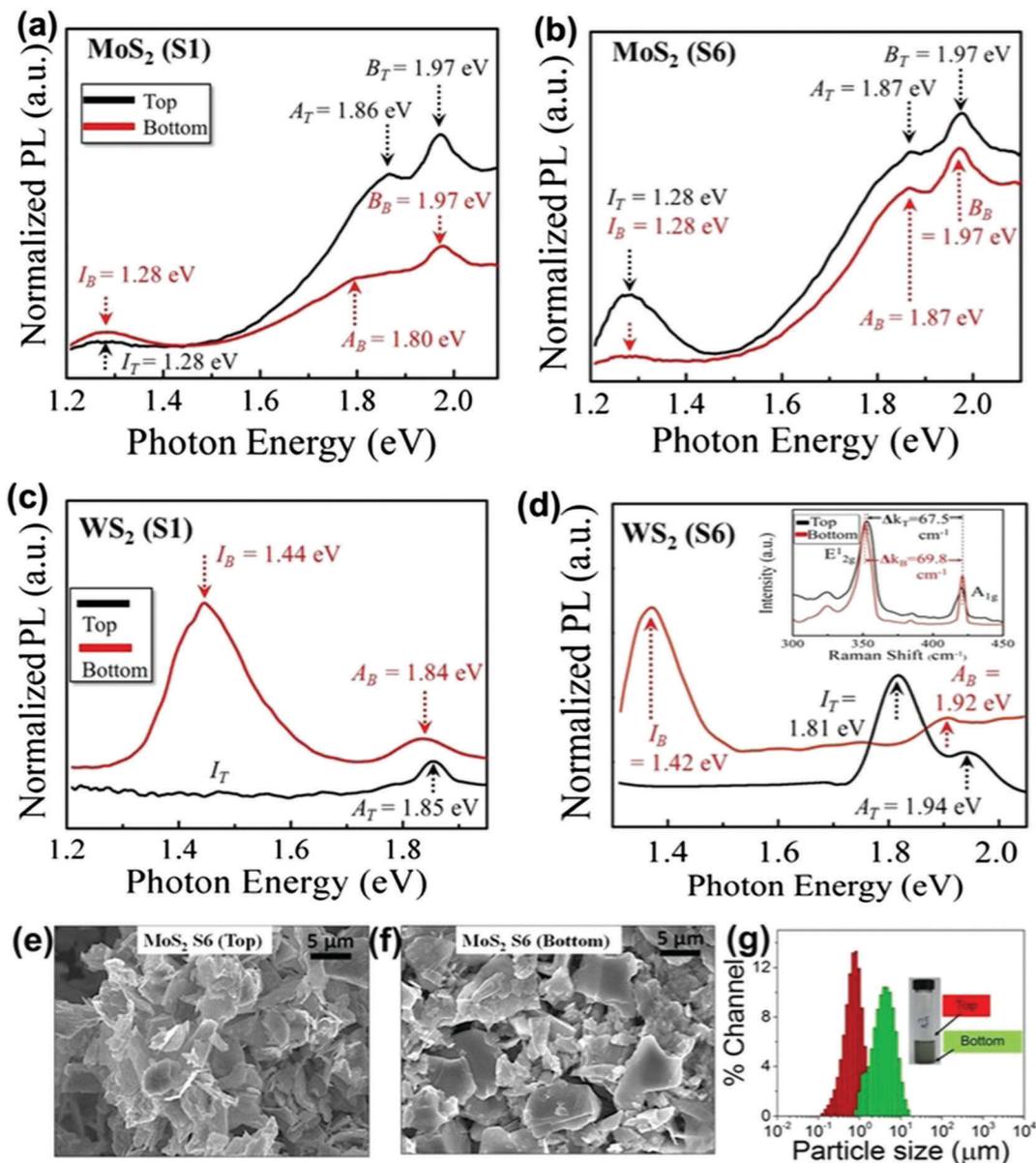


Fig. 4 (a) and (b) PL data corresponding to solution chemistries S1 (without terpineol) and S6 (with terpineol) for MoS₂, respectively, where the black spectra represent data gathered for MoS₂ nanomembranes taken from the top of the vial, and the red spectra correspond to materials taken from the bottom of the vial. For the peak coinciding with the monolayer emission A-peak,³³ we see a significant red shift from A_T ~ 1.86 eV and A_B ~ 1.80 eV, where broadening effects are also apparent for the A_B peak. This suggests that the dispersion chemistry S1 is not effective in exfoliating materials given the significant red-shift of ~ 60 meV between the top and bottom which is consistent with the red-shift of 100 meV computed for non-terpineol based dispersion using optical absorption spectroscopy, in close agreement with the PL data. The indirect-gap PL peak at I_B-I_T = 1.28 eV becomes more pronounced as the thickness increases which is once again an indication that the material taken from the bottom is composed of thicker layers than the material taken from the top. (b) PL data obtained for S6 for MoS₂, where terpineol appears to be effective in yielding a fewer layered material, where the red-shift effects are minimal since the location of A_T and A_B occur at 1.87 eV. (c) and (d) PL data corresponding to solution chemistries S1 and S6 for WS₂, respectively. The A-excitonic peak at the top and bottom yields A_T = 1.85 eV whereas A_B = 1.84 eV, indicating that the material taken from the bottom is slightly red shifted compared to the material taken from the top. The inset in (d) shows the Raman spectra for WS₂ where Δk_T ~ 67.5 cm⁻¹ between the out-of-plane A_{1g} mode and the in-plane E_{2g} mode for the material taken from the top, while Δk_B ~ 69.8 cm⁻¹ for the material taken from the bottom. The Δk_T ~ 67.5 cm⁻¹ is consistent with WS₂ being composed of bilayers.³⁴ High-resolution SEM imaging was conducted for MoS₂ for the material taken from the top of the vial in (e) and the morphology was compared to the material obtained from the bottom of the vial in (f) for S6. The SEM image in (f) clearly shows larger platelets, which are well above 5 μm in lateral dimensions, while the nanomembranes taken from the top of the vial shows the membranes to be thinner and smaller on average. (g) Particle size distribution of MoS₂ from the top and bottom for relative comparison. While the MoS₂ in this particular case was thermally treated for another experiment, a relative comparison shows distinct differences in particle size distribution for MoS₂ in a terpineol dispersion from the top and bottom, as indicated by the vial in the inset. The samples of MoS₂ taken from the top (red distribution) showed that the particle size has a Gaussian distribution with a mean particle size S_(top) ~ 0.8 μm (range = 0.1 to 3 μm), while for the samples taken from the bottom (green distribution), S_(bottom) ~ 5.5 μm (range = 1 to 20 μm).

The PL spectra for S6 in Fig. 4d shows the A_T peak occurring at a significantly larger energy ~ 1.94 eV, while the A_B peak is slightly red-shifted by ~ 20 meV since A_B occurs at ~ 1.92 eV, again suggestive of excitonic behavior occurring with thinner layers at the top. This is once again in close agreement with the optical absorption data reported for WS_2 in Fig. 2, where the red-shift was computed to be ~ 12 meV. The I_T peak was seen to be shifted toward higher energies at 1.81 eV compared to the I_B peak which was significantly red-shifted to 1.42 eV. The evolution of I_T to higher energies of ~ 1.81 eV is in excellent agreement with the PL data for WS_2 reported by Zhao *et al.*³⁴ and is suggestive of bilayer WS_2 membranes present in our terpeneol based dispersions. The bi-layer configuration of our terpeneol based dispersions is also corroborated by Raman spectroscopy analysis. The Raman spectra shown in the inset of Fig. 4d for WS_2 depicts the Raman shift $\Delta k_T \sim 67.5$ cm^{-1} between the out-of-plane A_{1g} mode and the in-plane E_{2g} mode for the material taken from the top, while $\Delta k_B \sim 69.8$ cm^{-1} for the material taken from the bottom. The $\Delta k_T \sim 67.5$ cm^{-1} is consistent with WS_2 being composed of bilayers. Zhao *et al.*³⁴ noted the evolution of electronic structure in atomically thin sheets of WS_2 where $\Delta k = 65.5$ cm^{-1} , 68.3 cm^{-1} and 69.2 cm^{-1} corresponds to monolayer, bilayer and trilayer WS_2 , respectively. In our case, the samples taken from the top of the vial show $\Delta k_T = 67.5$ cm^{-1} , which clearly indicates the presence of bilayer WS_2 in the terpeneol chemistry, again validating the promise of terpeneol to exfoliate 2D WS_2 effectively.

Besides PL analysis which supports our optical absorption analysis data, we also conducted high-resolution SEM imaging for MoS_2 for materials taken from the top of the vial (Fig. 4e), and this morphology was compared to materials taken from the bottom of the vial (Fig. 4f) for S6. The SEM image in Fig. 4f clearly shows larger platelets, which are well above 5 μm in lateral dimensions, while the nanomembranes taken from the top of the vial are composed of smaller and thinner platelets, on average. This morphological change was also corroborated with a particle size measurement technique (Fig. 4g) that was conducted using dynamic laser scattering (MicroTac), where the particle size distribution of MoS_2 was measured for materials taken from the top and bottom, as illustrated in the inset of Fig. 4g. While MoS_2 in this particular case was thermally treated for another experiment, a relative comparison shows distinct differences in particle size distribution for MoS_2 in a terpeneol dispersion from top and bottom. Samples of MoS_2 taken from the top (red distribution) showed that the particle size exhibited a Gaussian distribution with a mean particle size $S_{(top)} \sim 0.8$ μm (range = 0.1 to 3 μm), while for samples taken from the bottom (green distribution), $S_{(bottom)} \sim 5.5$ μm (range = 1 to 20 μm). This result is once again consistent with the optical absorption, PL, and SEM imaging analyses reported here.

As stated previously, the excitonic effects in 2D materials arise fundamentally from the large e-h pair binding energy that comes about from the strong Coulombic interaction in ultra-thin 2D nanosheets. In fact, this was elucidated in one of the early reports dating back to the 1970's by Consadori *et al.*³⁵ who showed the enhancement occurring in the A-peak, B-peak and

the A'-peak as mechanically exfoliated WSe_2 was thinned. This was attributed directly to the crystal size and quantum confinement effects operative in these systems. Subsequently, Mak *et al.*¹² and Splendiani *et al.*³⁶ built upon these concepts with PL and optical absorption spectroscopy analysis, where a strong enhancement in the PL intensity was seen for monolayer MoS_2 , as compared to thicker films. In all of these seminal investigations nonetheless, the origin of excitonic effects in 2D materials are directly related to crystal size and geometrical confinement effects in the quantum limit.

While geometrical confinement in the quantum limit can amplify excitonic behavior in 2D layered materials, crystalline disorder, defects, or strain, as well as doping can also influence the characteristics of the excitons.³⁷⁻⁴⁰ Intuitively, for a mechanically exfoliated monolayer 2D semiconducting crystal with a direct band gap one would expect a high PL yield. However, even for mechanically exfoliated monolayer MoS_2 , the PL quantum yield was measured to be far lower $\sim 4 \times 10^{-3}$ than expected for such pristine mechanically exfoliated crystallites.¹² The origin of this low quantum yield has been discussed in the context of unintentional doping in the naturally derived crystals, where exciton formation may be suppressed with potential non-radiative recombination pathways. The enhancement in excitonic effects we observe with terpeneol has thus far been discussed in the context of purely geometric crystal confinement effects, given terpeneol's ability to more effectively shear the crystal planes in 2D MoS_2 and WS_2 to thinner platelets, where the Coulombic interactions will be enhanced compared to our reference dispersion based on IPA. As Coleman's⁴¹ pioneering work on solution exfoliation points out, surface energy is an important parameter to gauge solvent efficacy. In fact modeling has shown that if the surface energy of the solvent is similar to that of the 2D material, the energy difference between the exfoliated and re-aggregated states will be very small, removing the driving force for re-aggregation.⁴¹ Specifically, for solvents with surface tensions close to 40 $mJ m^{-2}$, the enthalpy of mixing is minimized for most 2D materials where the surface energies are $\sim 60-70$ $mJ m^{-2}$. Interestingly, the surface tension of terpeneol (with EC) is ~ 42 $mJ m^{-2}$ ⁴² and thus appears to be well matched to the ideal value predicted from modeling, in contrast to the surface tension for IPA which is far lower ~ 22 $mJ m^{-2}$.

Additionally, given terpeneol's higher viscosity of ~ 40 cP at room temperature²⁴ compared to IPA (~ 2 cP), the rheological properties of the dispersions will also likely affect the degree of crystallinity, lattice distortion, defects and strain induced in the 2D materials, which can further suppress luminescence and excitonic effects. From our results, it is likely that given the better surface energy matching between terpeneol and 2D MoS_2 and WS_2 , coupled with its relatively higher viscosity even after mixing with IPA, the exfoliated nanosheets are likely composed of higher quality crystallites with fewer defects, which leads to more enhancement in excitonic effects in terpeneol-based dispersions, compared to IPA, for example. The role of defects in quenching the luminescence properties of 2D solution dispersions was recently investigated by Eda and co-workers²⁵ where MoS_2 crystals exfoliated using Li intercalation in butyl lithium

solution and hexane yielded excitonic peaks that were less resolved. This suppression of the peaks was attributed to residual structural disorder from the remnant lattice distortion, and at the same time a progressive increase in the emission intensity was observed with increasing annealing temperature, suggesting that the crystalline order was largely restored. Zhao *et al.*³⁴ also discussed the Stokes shift and the line-width of the emission peak in WS₂ and other 2D selenides, which was once again related to the crystalline quality. This finding is in alignment with our data for the terpeneol dispersions of MoS₂ for example, where we see minimal broadening in the A_B peak in Fig. 4b.

Finally, doping effects with our terpeneol-based dispersions can also not be ruled out completely, particularly based on recent reports where doping was seen to influence the excitonic binding energy for MoS₂.³⁷ Similarly, Mouri *et al.*⁴³ showed an increase in the PL intensity in MoS₂ when p-type dopants derived from tetrafluorotetracyanoquinodimethane (F4TCNQ) and tetracyanoquinodimethane (TCNQ) were drop cast onto MoS₂. They discussed the excitonic enhancement in the context of exciton and charge carrier dynamics which gives rise to the formation of a many-body bound state, a charged exciton or trion, and a shift in the Fermi level was also induced. While doping effects may be operative in our solution dispersions of terpeneol, more detailed characterization of the excitonic dynamics would be necessary to elucidate the exact mechanisms.

We have also conducted two-terminal electronic transport measurements for the 2D MoS₂ dispersions of S3 and S5 solutions that are drop cast onto SiO₂/Si substrates, as shown in Fig. 4. A mechanically exfoliated MoS₂ sample, denoted as m-MoS₂, was also prepared for comparative analysis, and this data is also shown in Fig. 4. In order to electrically contact the m-MoS₂ and the drop cast samples, MoS₂-S3 and MoS₂-S5, electrodes of Mo metal were sputtered onto SiO₂/Si substrates, at a thickness of 100 nm and patterned lithographically. For the m-MoS₂ sample, the mechanically exfoliated flakes were placed on top of the Mo contacts. For the drop cast MoS₂-S3 and MoS₂-S5 samples, annealing was conducted at 400 °C for 30 min in air. The *I*-*V* transport data were captured using a low-noise semiconductor parameter analyzer (Agilent 4156A) interfaced to a micro-manipulator probe stage, and tungsten (W) probe tips were used with a probe spacing of 16 μm, 18 μm, and 500 μm for the MoS₂-S3, MoS₂-S5, and m-MoS₂ samples, respectively. The inset in Fig. 4a depicts the transport characteristics of the m-MoS₂ sample measured over a wider voltage range prior to current saturation. From these data, we note that the magnitude of the current in S5 is larger than that of the S3 dispersion by more than 10× (*e.g.* at 5 V the current increases from 7 nA for S3 to 460 nA for S5) for similar device geometries. We believe that this enhancement in the electronic transport properties can be correlated to the role of the EC and T in yielding effective dispersions, and enhancing the excitonic peaks as also noted from the optical absorption spectra of MoS₂ for the S5 sample.

While there has been prior work on the field-effect-transistor (FET) behavior in chemically and mechanically exfoliated 2D materials,^{4,44} analysis of the transport mechanism in drop cast 2D MoS₂ has been minimal to date, which we now discuss here

in more detail. The *I*-*V* characteristics generally show an exponential conduction mechanism which can be expressed as $I(V) = I_0 (\exp(\alpha V) - 1)$ for thermionic emission, where I_0 is the saturation current and α is a fitting parameter. The *I*-*V* data in Fig. 4a can be fitted to the Levenberg-Marquardt algorithm (least-squares method) when the measurement is reversible and noise is not taken into account. From the fitting of the *I*-*V* characteristics in the forward sweep mode of the MoS₂-S5 sample, we extract $I_0 \sim 2.5 \mu\text{A}$ and $\alpha \sim 0.04$ (with $R^2 = 0.99949$). Other possible modes of conduction that exhibit an exponential dependence on the voltage include tunneling, generation-recombination mechanisms, and Schottky behavior,⁴⁵ but in our analysis we found that the thermionic emission provided a reasonable fit for the MoS₂-S5 sample. In the case of m-MoS₂ and MoS₂-S3 samples, a single fit to any one of the three exponential behaviors was not possible. In the latter two cases, the conduction mechanism seems to be a double-diode with two conduction mechanisms probably due to the Mo-MoS₂ Schottky contacts that exhibit no series resistance. Because the work function ϕ_0 of the W (probes) and Mo (electrodes) is ~ 4.3 - 5.2 eV and ~ 4.36 - 4.95 eV, respectively, which is close to $\phi_0 \sim 4.6$ - 4.9 eV for MoS₂, we are unable to conclusively verify that a Schottky-barrier exists between MoS₂ and Mo. In prior work that considered Au and Ti contacts to MoS₂, factors such as annealing, contact metal deposition parameters, and surface cleanliness,⁴⁶ were all deemed important in controlling the interfacial work function to reduce the contact resistance in FET devices. Incidentally, Kang *et al.* reported on the formation of high-quality Mo-MoS₂ interfaces.⁴⁷

Besides looking at the electronic transport characteristics of the 2D drop-cast dispersions of MoS₂, we also formed p-n junction devices where the drop-cast 2D MoS₂-S5 dispersion was placed on p-type Si substrates, as shown in Fig. 5b-d. Tungsten probes were used to measure the conductivity between the p-Si anode and the presumed n-type solution dispersed MoS₂ cathode. Here, the samples were annealed as previously described (at 400 °C for 30 min in air). As shown by the data in Fig. 5b-d, we elucidate the effect of solution chemistry on the device parameters, specifically leakage current I_0 and turn on voltage, V_T . The *I*-*V* data for solution chemistry S5, S1 and S6 are shown in Fig. 5b, c and d, respectively, where the inks were dispersed onto heavily doped p-type Si substrates. The figures of merit for the devices are summarized in (e) which indicate that the solution chemistry S6 yields the lowest V_T of ~ 2 V, as compared to S5 which has a V_T of ~ 4.87 V and S1 which has a $V_T \sim 11$ V; the leakage currents for both of the terpeneol derived solution chemistries, S5 and S6 yield $I_0 \sim$ on the order of 10-90 nA at 10 V, whereas the I_0 for S1 is $\sim 2 \mu\text{A}$, which is approximately two orders of magnitude larger. All of these data once again validate the effectiveness of terpeneol in enabling 2D dispersions that yield enhanced transport properties, which is also consistent with the enhanced excitonic effects observed in this particular solution chemistry. The transport behavior of our p-n junction devices and V_T values are similar to that reported by Jeong *et al.*⁴⁸ for MoS₂/p-GaN. Also in the reverse bias regime, Jeong *et al.*⁴⁸ did not see distinct rectification,

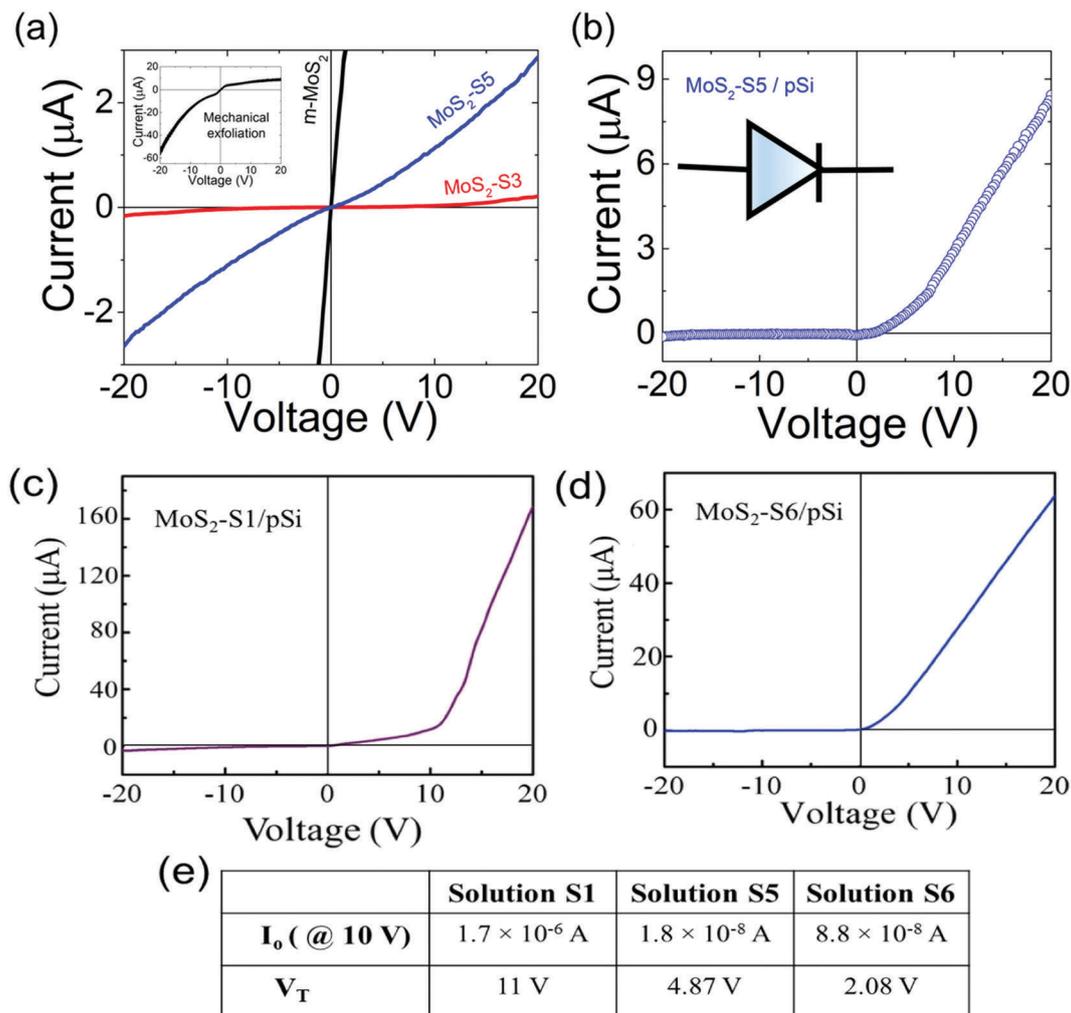


Fig. 5 (a) I - V characteristics of mechanically exfoliated m - MoS_2 and a drop cast MoS_2 dispersed under the conditions of S3 with Mo electrodes (red) and MoS_2 dispersed under the conditions of S5 (blue) deposited on SiO_2/Si . (b) I - V characteristics of the p - n junction formed with MoS_2 -S5 on doped p -Si substrates showing current rectification in the reverse bias regime with $V_T \sim 4.87$ V. The inset shows the symbol for a two-terminal current rectifying diode. (c) and (d) I - V data for solution chemistries S1 and S6 where the inks were dispersed onto heavily doped p -type Si substrates, similar to the data obtained in (b). We see the effect of solution chemistry on the device parameters, specifically leakage current I_0 and turn on voltage, V_T . The figures of merit for the devices summarized in (e) indicate that the solution chemistry S6 yields the lowest V_T of ~ 2 V, as compared to S5 which has a turn on voltage of ~ 4.87 V and S1 with $V_T \sim 11$ V; the leakage currents for both of the terpeneol derived solution chemistries S5 and S6 yield $I_0 \sim$ on the order of 10–90 nA, whereas the I_0 for S1 is ~ 2 μA , which is approximately two orders of magnitude larger. All of these data once again validate the effectiveness of terpeneol in enabling 2D dispersions that yield enhanced transport properties, which is also consistent with the enhanced excitonic effects observed in this particular solution chemistry.

as we observe here in all three solution chemistries. The current behavior in our devices can be explained on the basis of the conventional p - n junction theory. In the forward bias regime (p -Si positively biased), the current scales exponentially with the height of potential barrier for $V > V_T$.⁴⁹ In the reverse bias regime (p -Si negatively biased), the depletion region increases and a weak leakage current flows through the junction in this reverse bias regime.

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